

MOSFETs Silicon N-Channel MOS ( $\pi$ -MOSVIII)

# TK9A90E

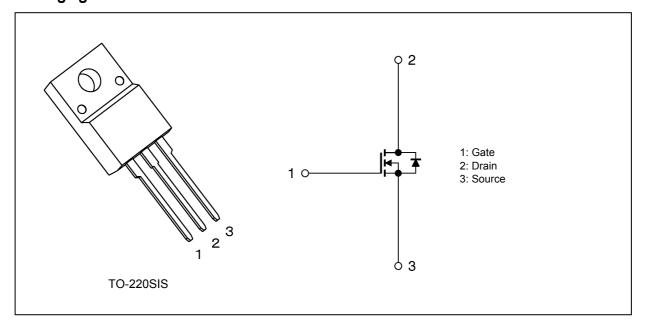
#### 1. Applications

• Switching Voltage Regulators

#### 2. Features

- (1) Low drain-source on-resistance:  $R_{DS(ON)} = 1.0 \Omega$  (typ.)
- (2) Low leakage current :  $I_{DSS}$  = 10  $\mu A$  (max) ( $V_{DS}$  = 720 V)
- (3) Enhancement mode:  $V_{th}$  = 2.5 to 4.0 V ( $V_{DS}$  = 10 V,  $I_{D}$  = 0.9 mA)

#### 3. Packaging and Internal Circuit





## 4. Absolute Maximum Ratings (Note) (Ta = 25 °C unless otherwise specified)

Characteristics	Symbol	Rating	Unit	
Drain-source voltage		V <sub>DSS</sub>	900	V
Gate-source voltage	,	V <sub>GSS</sub>	±30	
Drain current (DC)	(Note 1)	I <sub>D</sub>	9	Α
Drain current (pulsed)	(Note 1)	I <sub>DP</sub>	27	
Power dissipation	(T <sub>c</sub> = 25°C)	P <sub>D</sub>	50	W
Single-pulse avalanche energy	(Note 2)	E <sub>AS</sub>	454	mJ
Avalanche current		I <sub>AR</sub>	9	Α
Reverse drain current (DC)	(Note 1)	I <sub>DR</sub>	9	
Reverse drain current (pulsed)	(Note 1)	I <sub>DRP</sub>	27	
Channel temperature		T <sub>ch</sub>	150	°C
Storage temperature	,	T <sub>stg</sub>	-55 to 150	
Isolation voltage (RMS)		V <sub>ISO(RMS)</sub>	2000	V
Mounting torque		TOR	0.6	N · m

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### 5. Thermal Characteristics

Characteristics	Symbol	Max	Unit
Channel-to-case thermal resistance	R <sub>th(ch-c)</sub>	2.5	°C/W
Channel-to-ambient thermal resistance		62.5	

Note 1: Ensure that the channel temperature does not exceed 150 °C.

Note 2:  $V_{DD}$  = 90 V,  $T_{ch}$  = 25°C (initial), L = 10.3 mH,  $R_G$  = 25  $\Omega$ ,  $I_{AR}$  = 9 A

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.



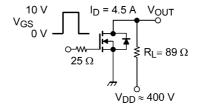
#### 6. Electrical Characteristics

## 6.1. Static Characteristics (T<sub>a</sub> = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I <sub>GSS</sub>	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±1	μΑ
Drain cut-off current	I <sub>DSS</sub>	V <sub>DS</sub> = 720 V, V <sub>GS</sub> = 0 V	_	_	10	
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V	900	_	_	V
Gate threshold voltage	V <sub>th</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 0.9 mA	2.5	_	4.0	
Drain-source on-resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 4.5 A	_	1.0	1.3	Ω

#### 6.2. Dynamic Characteristics (T<sub>a</sub> = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V, f = 1 MHz	_	2000	_	pF
Reverse transfer capacitance	$C_{rss}$		_	15		
Output capacitance	C <sub>oss</sub>		_	150		
Gate resistance	r <sub>g</sub>	V <sub>DS</sub> = OPEN, f = 1 MHz	_	3.5		Ω
Switching time (rise time)	t <sub>r</sub>	See Fig. 6.2.1.	_	40		ns
Switching time (turn-on time)	t <sub>on</sub>		_	80		
Switching time (fall time)	t <sub>f</sub>		_	35		
Switching time (turn-off time)	t <sub>off</sub>		_	140	_	
MOSFET dv/dt ruggedness	dv/dt	$V_{DD} = 0 \text{ to } 400 \text{ V}, I_D = 9 \text{ A}$	20	_	_	V/ns



Duty  $\leq$  1%,  $t_W^{}=$  10  $\mu s$ 

Fig. 6.2.1 Switching Time Test Circuit

### 6.3. Gate Charge Characteristics (T<sub>a</sub> = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	$Q_g$	$V_{DD} \approx 400 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 9 \text{ A}$		46		nC
Gate-source charge 1	Q <sub>gs1</sub>			13		
Gate-drain charge	$Q_{gd}$		_	18	_	

## 6.4. Source-Drain Characteristics (T<sub>a</sub> = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Diode forward voltage	V <sub>DSF</sub>	I <sub>DR</sub> = 9 A, V <sub>GS</sub> = 0 V	_	_	-1.7	V
Reverse recovery time	t <sub>rr</sub>	I <sub>DR</sub> = 9 A, V <sub>GS</sub> = 0 V	_	1200	_	ns
Reverse recovery charge	Q <sub>rr</sub>	-dI <sub>DR</sub> /dt = 100 A/μs	_	12	_	μС
Peak reverse recovery current	I <sub>rr</sub>		_	24	_	Α



## 7. Marking (Note)

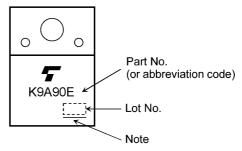


Fig. 7.1 Marking

Note: A line under a Lot No. identifies the indication of product Labels.

Not underlined: [[Pb]]/INCLUDES > MCV

Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product.

The RoHS is the Directive 2011/65/EU of the European Parliament and of the Council of 8 June 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

#### 8. Characteristics Curves (Note)

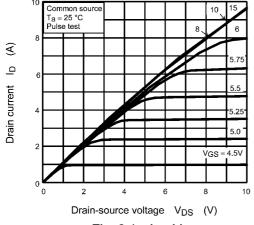
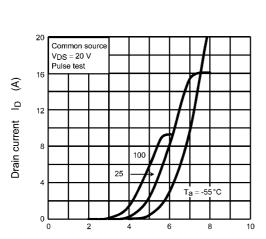


Fig. 8.1  $I_D - V_{DS}$ 



Gate-source voltage  $V_{GS}$  (V) Fig. 8.3 I<sub>D</sub> - V<sub>GS</sub>

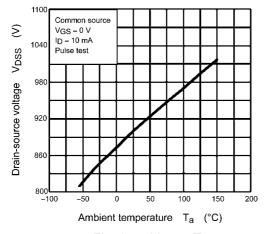


Fig. 8.5 V<sub>DSS</sub> - T<sub>a</sub>

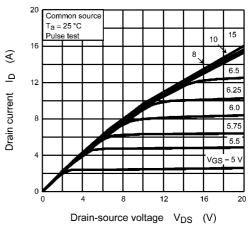


Fig. 8.2 I<sub>D</sub> - V<sub>DS</sub>

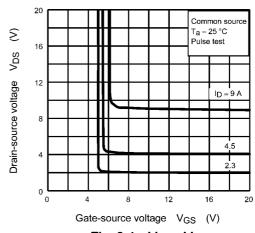


Fig. 8.4 V<sub>DS</sub> - V<sub>GS</sub>

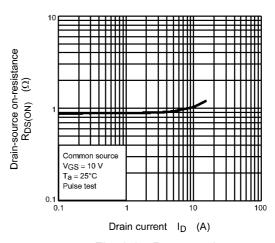


Fig. 8.6  $R_{DS(ON)}$  -  $I_D$ 

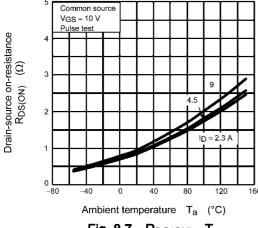


Fig. 8.7 R<sub>DS(ON)</sub> - T<sub>a</sub>

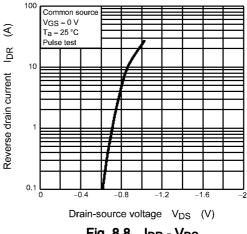


Fig. 8.8 I<sub>DR</sub> - V<sub>DS</sub>

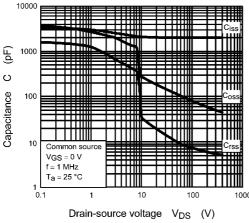


Fig. 8.9 C - V<sub>DS</sub>

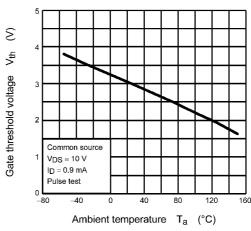


Fig. 8.10 V<sub>th</sub> - T<sub>a</sub>

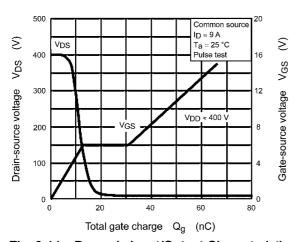


Fig. 8.11 Dynamic Input/Output Characteristics

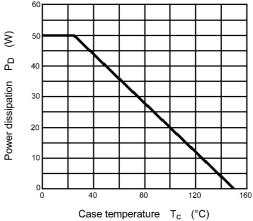


Fig. 8.12 P<sub>D</sub> - T<sub>c</sub> (Guaranteed Maximum)

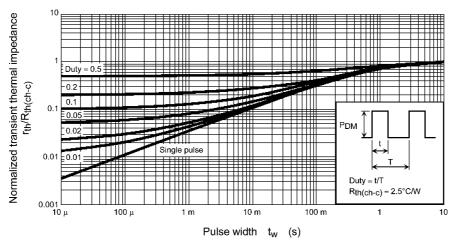


Fig. 8.13 r<sub>th</sub> - t<sub>w</sub> (Guaranteed Maximum)

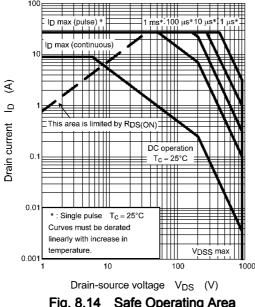


Fig. 8.14 Safe Operating Area (Guaranteed Maximum)

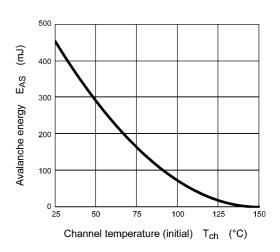


Fig. 8.15 E<sub>AS</sub> - T<sub>ch</sub> (Guaranteed Maximum)

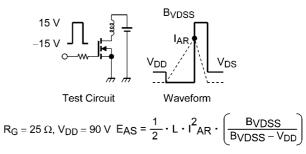


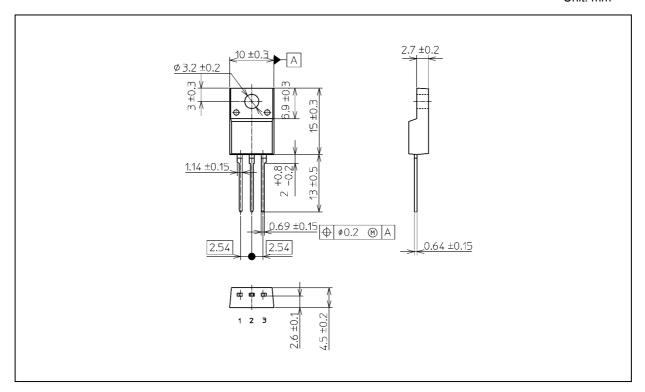
Fig. 8.16 Test Circuit/Waveform

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



## **Package Dimensions**

Unit: mm



Weight: 1.7 g (typ.)

Pac	ckage Name(s)
JEITA: SC-67	
TOSHIBA: 2-10U1S	
Nickname: TO-220SIS	



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2014-03-04

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